



VDRM

T(AV)

Iтsм dV/dt\*

dl/dt

**KEY PARAMETERS** 

8500V

2450A

33500A

1500V/µs

300A/µs

\* Higher dV/dt selections are available on request



### Replaces DS6077-3

Phase Control Thyristor

DS6077-4	May 2022	(LN41730)

## FEATURES

- Double Side Cooling
- High Surge Capability

## **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

## **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages Vdrm and Vrrm (V)	Conditions
		Tvj = -40°C to 125°C,
DCR2450W85*	8500	Idrm = Irrm = 300mA,
DCR2450W80	8000	Vdrm, Vrrm tp = 10ms
DCR2450W75	7500	Vdsm & Vrsm =
DCR2450W70	7000	Vdrm & Vrrm + 100V
		respectively

Lower voltage grades available.

\*8200V @ -40°C, 8500V @ 0°C

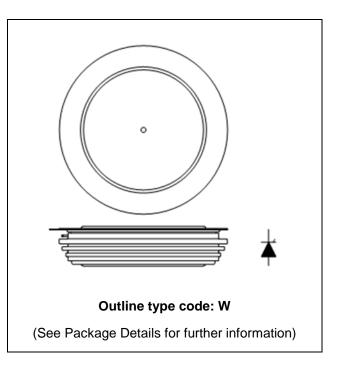
## **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

## DCR2450W85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.



## Fig. 1 Package outline

## **CURRENT RATINGS**

T<sub>case</sub> = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
Ιτ(Αν)	Mean on-state current	Half wave resistive load	2450	А
It(rms)	RMS value	-	3850	А
Іт	Continuous (direct) on-state current	-	3750	А

## SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, Tcase = 125°C	33.5	kA
l²t	I <sup>2</sup> t for fusing	VR = 0	5.61	MA <sup>2</sup> s

# THERMAL AND MECHANICAL RATINGS

Symbol	Parameter Test Conditions			Min.	Max.	Units
		Double side cooled	DC	-	6.3	°C/kW
Rth(j-c)	Thermal resistance - junction to case		Anode DC	-	11.2	°C/kW
		Single side cooled	Cathode DC	-	14.5	°C/kW
Balan	Thermal registeres access to heateink	Clamping force 76kN	Double side	-	1.4	°C/kW
r∖tn(c-h)	Rth(c-h) Thermal resistance - case to heatsink	(with mounting compound)	Single side	-	2.8	°C/kW
Tvj	Virtual junction temperature	Blocking VDRM / VRRM		-	125	°C
Tstg	Storage temperature range	age temperature range		-55	125	°C
Fm	Clamping force			68	84	kN

# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Condition	IS	Min.	Max.	Units
Irrm/Idrm	Peak reverse and off-state current	At Vrrm/Vdrm, Tcase = 125°C	;	-	300	mA
Vтм	Instantaneous forward voltage	At 4000A peak, Tj = 125°C		2.50	2.85	V
dV/dt	Max. linear rate of rise of off-state voltage	То 67% Vdrm, Tj = 125°C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% VDRM to 2x $I_{T(AV)}$ Gate source 30V, 10 $\Omega$	Repetitive 50Hz	-	150	A/µs
anat			Non-repetitive	-	300	A/µs
Veren	Threshold voltage - Low level	500A to 2500A at T <sub>case</sub> = 125°C		-	1.04	V
<b>V</b> τ(το)	Threshold voltage - High level 2500A to 7000A at T <sub>case</sub> = 125°C		-	1.29	V	
_	On-state slope resistance - low level	500A to 2500A at T <sub>case</sub> = 125°C		-	0.49	mΩ
ľΤ	On-state slope resistance - High level	2500A to 7000A at T <sub>case</sub> = 125°C		-	0.39	mΩ
tgd	Delay time	V <sub>D</sub> = 67% V <sub>DRM</sub> , gate source 30V, 10Ω tr = 0.5μs, Tj = 25°C		-	3	μs
tq	Turn-off time	Tj = 125°C, V <sub>R</sub> = 200V, dl/dt = 1A/µs, dV <sub>DR</sub> /dt = 20V/µs linear		-	1000	μs
Qs	Stored charge	Iτ = 2000A, Tj = 125°C, dl/dt = 1A/μs		6200	9030	μC
Irr	Reverse recovery current	VR(peak) ~ 5100V, VRM ~ 3400V		59	70	А
lı.	Latching current	Tj = 25°C, VD = 5V		-	3	А
Ін	Holding current	Тј = 25°С, R <sub>G-</sub> к = ∞, Iтм = 50	0A, I⊤ = 5A	-	300	mA

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# GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Vgт	Gate trigger voltage	Vdrm = 5V, Tcase = 25°C	1.5	V
Vgd	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
Іст	Gate trigger current	VDRM = 5V, Tcase = 25°C	400	mA
Igd	Gate non-trigger current	At 50% Vdrm, Tcase = 125°C	10	mA

# CURVES

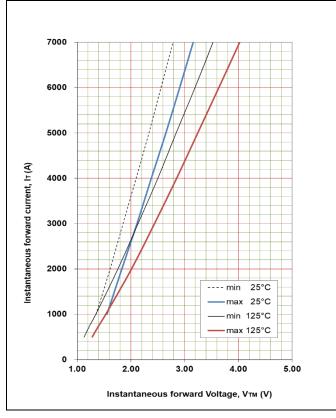


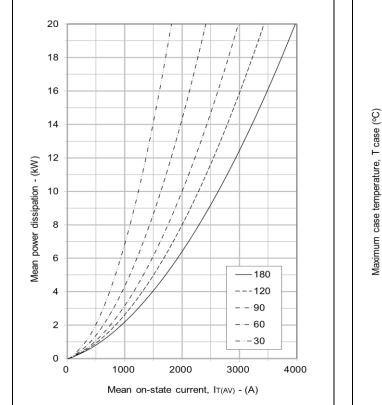
Fig. 2 Maximum & minimum on-state characteristics

# **VTM EQUATION**

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$ 

Where A = 1.027695B = -0.040022C = 0.000289D = 0.015761These values are valid for T<sub>j</sub> =  $125^{\circ}$ C for I<sub>T</sub> 500A to 7000A

## DCR2450W85



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Fig. 3 On-state power dissipation - sine wave

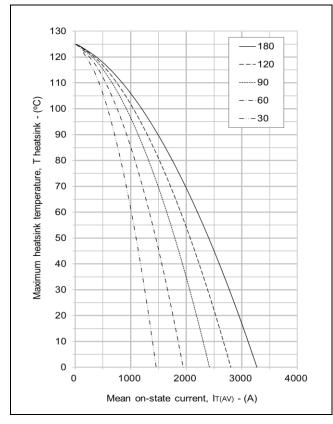


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

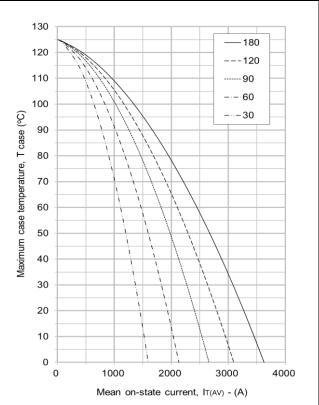


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

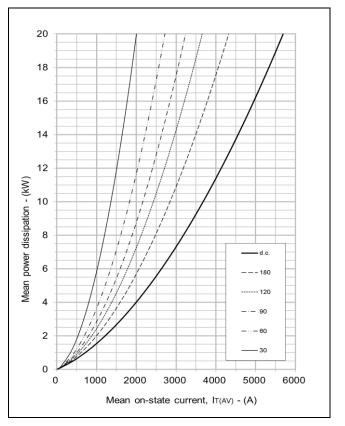
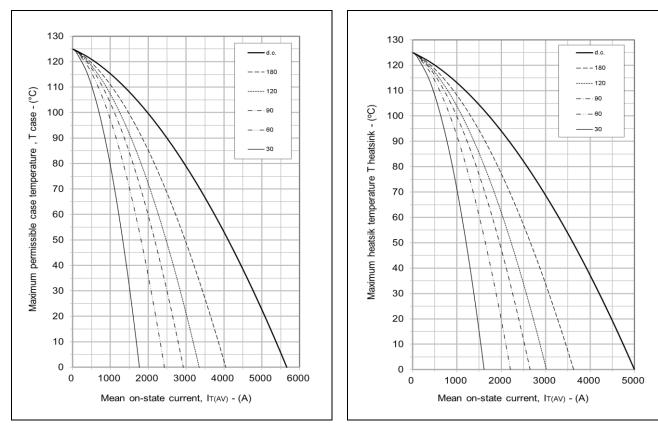


Fig. 6 On-state power dissipation - rectangular wave



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Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave

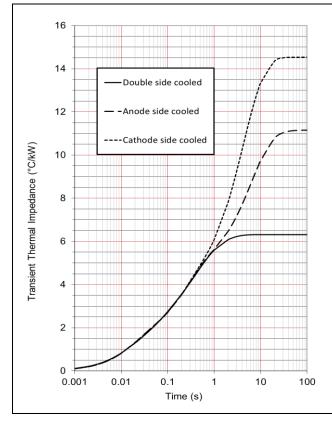


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	0.882	1.299	2.805	1.331
cooled	Ti(s)	0.011	0.058	0.358	1.129
Anode side	Ri(°C/kW)	1.520	3.240	5.762	0.631
cooled	Ti(s)	0.017	0.242	6.013	15.364
Cathode side	Ri(°C/kW)	1.411	2.467	6.745	3.905
cooled	Ti(s)	0.016	0.179	3.620	6.196

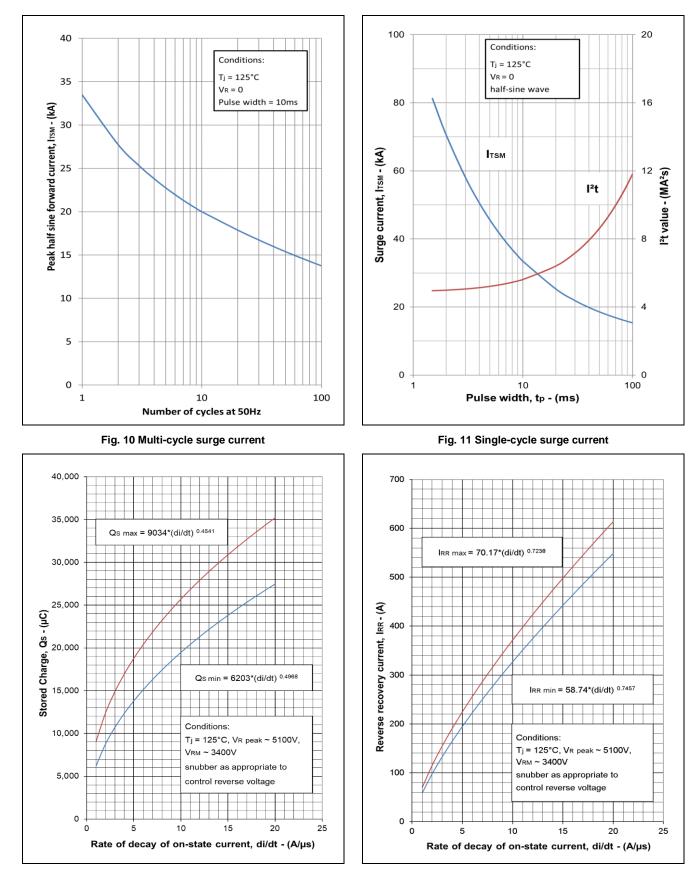
$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{th(j-c)}$  Conduction

Tables show the increments of thermal resistance R  $_{\text{trij-e}}$  when the device operates at conduction angles other than d.c.

	Double side co	oling			Anode Side Cooling			Cathode Sided Cooling		
	ΔZ <sub>th</sub>	(Z)			$\Delta Z_{th}(z)$				$\Delta Z_{th}(z)$	
θ°	sine.	rect.	l L	θ°	sine.	rect.		θ°	sine.	rect.
180	1.00	0.67		180	0.94	0.64		180	0.95	0.65
120	1.16	0.97		120	1.08	0.91		120	1.09	0.92
90	1.33	1.13	L	90	1.23	1.06		90	1.25	1.07
60	1.48	1.31		60	1.37	1.22		60	1.38	1.23
30	1.61	1.51		30	1.47	1.38		30	1.49	1.40
15	1.66	1.61		15	1.52	1.47		15	1.54	1.49

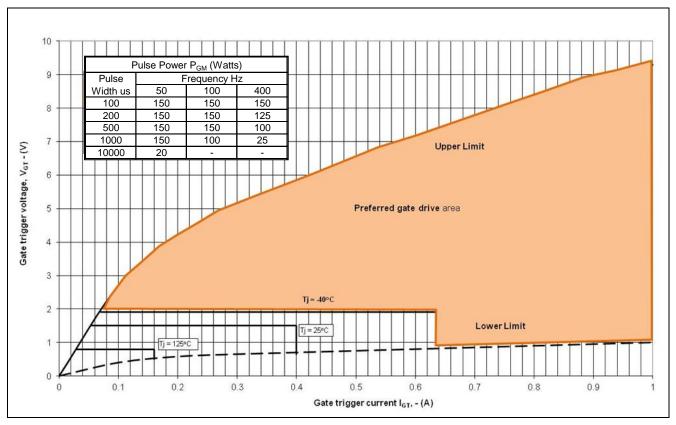
Fig. 9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)



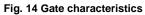
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Fig. 12 Reverse recovery charge

Fig. 13 Reverse recovery current



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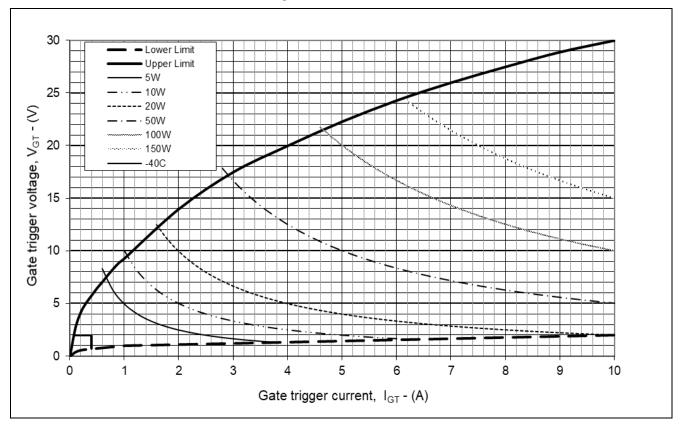


Fig. 15 Gate characteristics

## PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

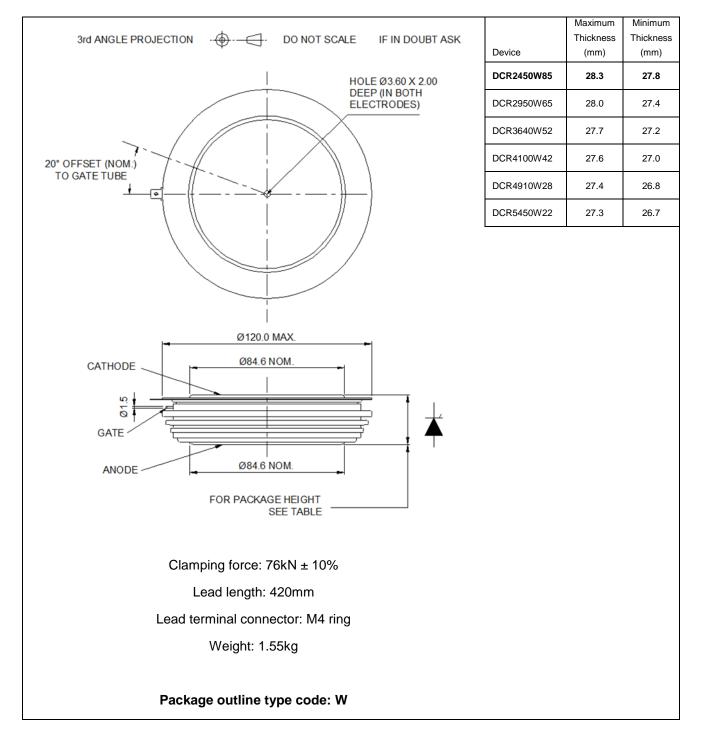


Fig. 16 Package outline

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